

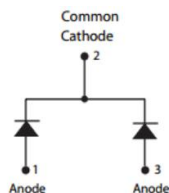
STW30200C SCHOTTKY RECTIFIER



Features

- 150 °C T_J operation
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	200	V
Average Rectified Forward Current	I _{F(AV)}	50% duty cycle @T _c =100°C, rectangular wave form	15(Per Leg) 30(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	200	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop(Per Leg)*	V _{F1}	@ 5A, Pulse, T _J = 25 °C	0.70	-	V
		@ 10A, Pulse, T _J = 25 °C	0.78	-	
		@ 15A, Pulse, T _J = 25 °C	0.81	1.10	
	V _{F2}	@ 5A, Pulse, T _J = 125 °C	0.56	-	V
		@ 15A, Pulse, T _J = 125 °C	0.61	-	
		@ 15A, Pulse, T _J = 125 °C	0.68	0.72	
Reverse Current(Per Leg)*	I _{R1}	@V _R = rated V _R , T _J = 25°C	0.0005	0.16	mA
	I _{R2}	@V _R = rated V _R , T _J = 125°C	1	12	mA
Junction Capacitance	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	300	-	pF

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case(Per Leg)	$R_{\theta JC}$	DC operation	1.6	$^{\circ}\text{C/W}$
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

Ratings and Characteristics Curves

Figure 1
Typical Forward Characteristics

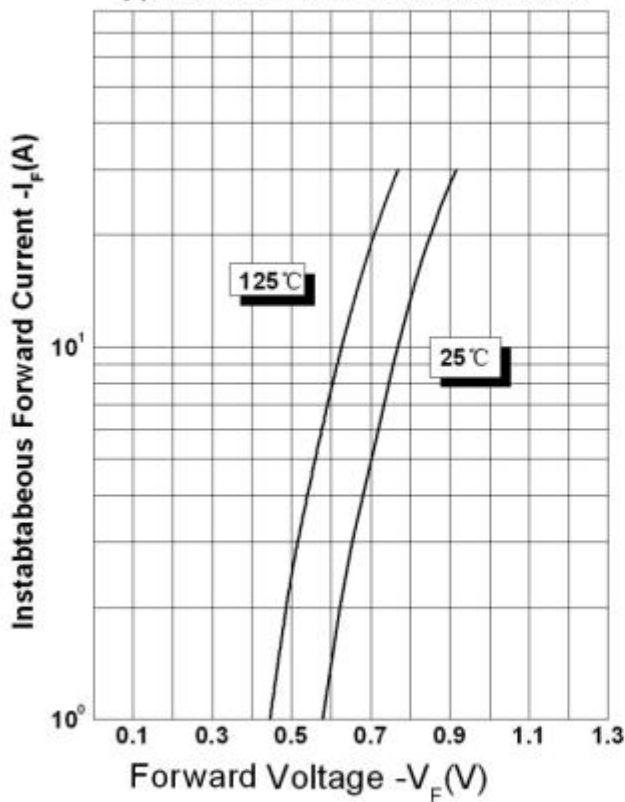


Figure 2
Typical Reverse Characteristics

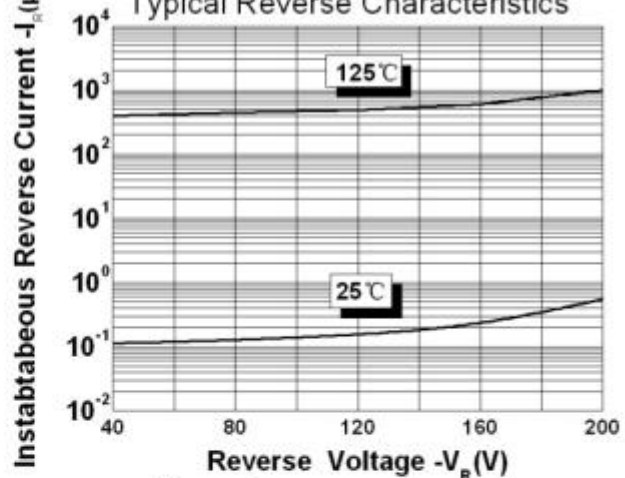
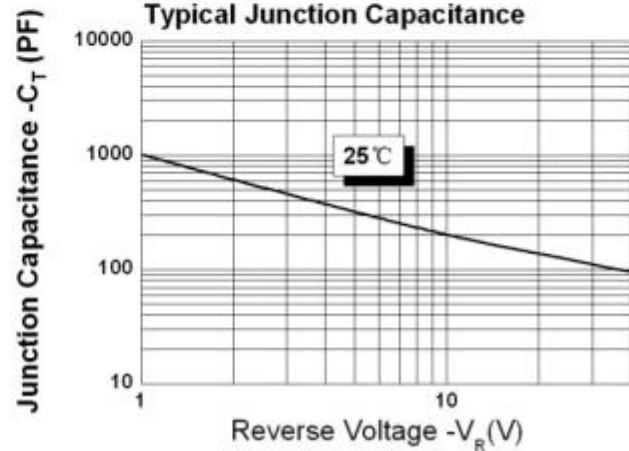
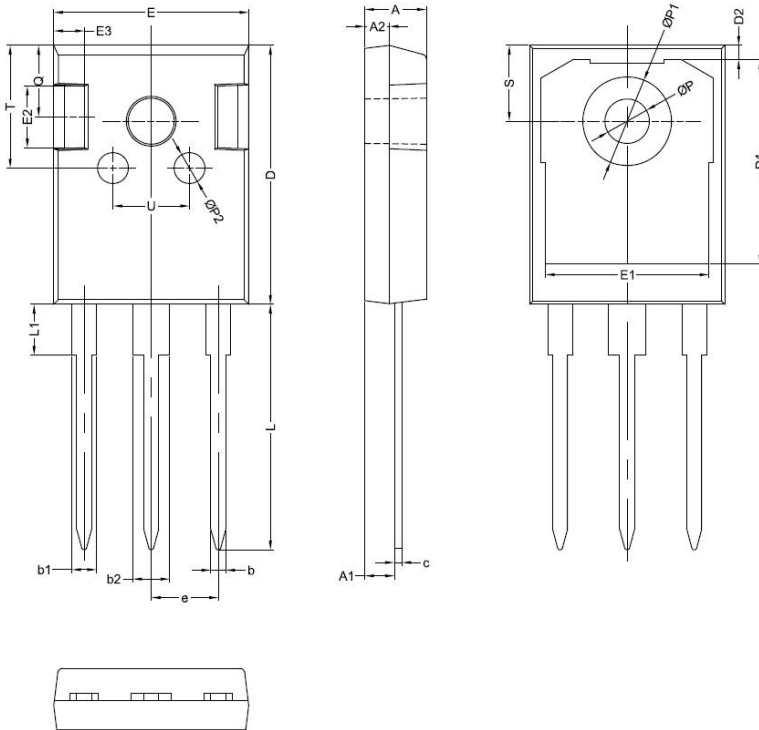


Figure 3
Typical Junction Capacitance



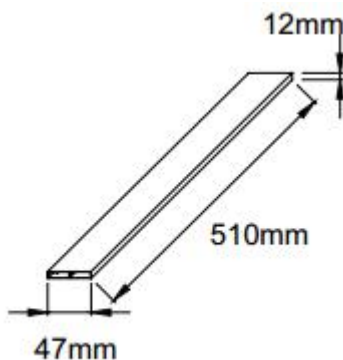
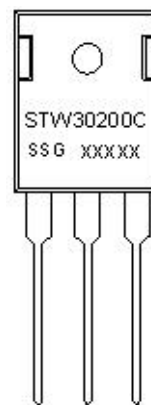
Mechanical Dimensions TO-247AD


SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.40
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.55	
D2		1.20	
E	15.45	15.80	16.00
E1		13.30	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.70
L1		4.13	
P	3.50	3.60	3.70
P1	7.1		7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

Ordering Information:

Device	Package	Shipping
STW30200C	TO-247AD(Pb-Free)	25pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Tube Specification

Marking Diagram


Where XXXXX is YYWWL

S = Device Type
 T = Ultralow VF
 W = Package type
 30 = Forward Current (30A)
 200 = Reverse Voltage (200V)
 C = Configuration
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

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